

# MMBTA92LT1

Preferred Device

## High Voltage Transistor

### PNP Silicon

#### Features

- Pb-Free Package May be Available. The G-Suffix Denotes a Pb-Free Lead Finish

#### MAXIMUM RATINGS

Rating	Symbol	MMBTA92	Unit
Collector–Emitter Voltage	$V_{CEO}$	–300	Vdc
Collector–Base Voltage	$V_{CBO}$	–300	Vdc
Emitter–Base Voltage	$V_{EBO}$	–5.0	Vdc
Collector Current – Continuous	$I_C$	–500	mAdc

#### THERMAL CHARACTERISTICS

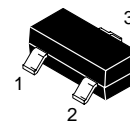
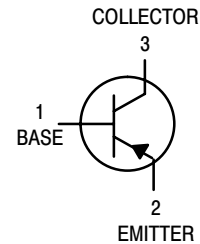
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board, (Note 1) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	$T_J, T_{stg}$	–55 to +150	$^\circ\text{C}$

- FR–5 = 1.0 x 0.75 x 0.062 in.
- Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.



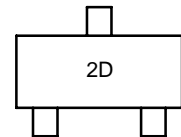
ON Semiconductor®

<http://onsemi.com>



SOT–23 (TO–236AF)  
CASE 318  
Style 6

#### MARKING DIAGRAM



2D = Specific Device Code

#### ORDERING INFORMATION

Device	Package	Shipping†
MMBTA92LT1	SOT–23	3000 / Tape & Reel
MMBTA92LT1G	SOT–23	3000 / Tape & Reel
MMBTA92LT3	SOT–23	10000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

# MMBTA92LT1

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector–Emitter Breakdown Voltage (Note 3) ( $I_C = -1.0\text{ mAdc}$ , $I_B = 0$ )	$V_{(BR)CEO}$	-300	-	Vdc
Collector–Base Breakdown Voltage ( $I_C = -100\ \mu\text{Adc}$ , $I_E = 0$ )	$V_{(BR)CBO}$	-300	-	Vdc
Emitter–Base Breakdown Voltage ( $I_E = -100\ \mu\text{Adc}$ , $I_C = 0$ )	$V_{(BR)EBO}$	-5.0	-	Vdc
Collector Cutoff Current ( $V_{CB} = -200\text{ Vdc}$ , $I_E = 0$ )	$I_{CBO}$	-	-0.25	$\mu\text{Adc}$
Emitter Cutoff Current ( $V_{EB} = -3.0\text{ Vdc}$ , $I_C = 0$ )	$I_{EBO}$	-	-0.1	$\mu\text{Adc}$
<b>ON CHARACTERISTICS (Note 3)</b>				
DC Current Gain ( $I_C = -1.0\text{ mAdc}$ , $V_{CE} = -10\text{ Vdc}$ ) ( $I_C = -10\text{ mAdc}$ , $V_{CE} = -10\text{ Vdc}$ ) ( $I_C = -30\text{ mAdc}$ , $V_{CE} = -10\text{ Vdc}$ )	$h_{FE}$	25 40 25	- - -	-
Collector–Emitter Saturation Voltage ( $I_C = -20\text{ mAdc}$ , $I_B = -2.0\text{ mAdc}$ )	$V_{CE(sat)}$	-	-0.5	Vdc
Base–Emitter Saturation Voltage ( $I_C = -20\text{ mAdc}$ , $I_B = -2.0\text{ mAdc}$ )	$V_{BE(sat)}$	-	-0.9	Vdc
<b>SMALL–SIGNAL CHARACTERISTICS</b>				
Current–Gain – Bandwidth Product ( $I_C = -10\text{ mAdc}$ , $V_{CE} = -20\text{ Vdc}$ , $f = 100\text{ MHz}$ )	$f_T$	50	-	MHz
Collector–Base Capacitance ( $V_{CB} = -20\text{ Vdc}$ , $I_E = 0$ , $f = 1.0\text{ MHz}$ )	$C_{cb}$	-	6.0	pF

3. Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

# MMBTA92LT1

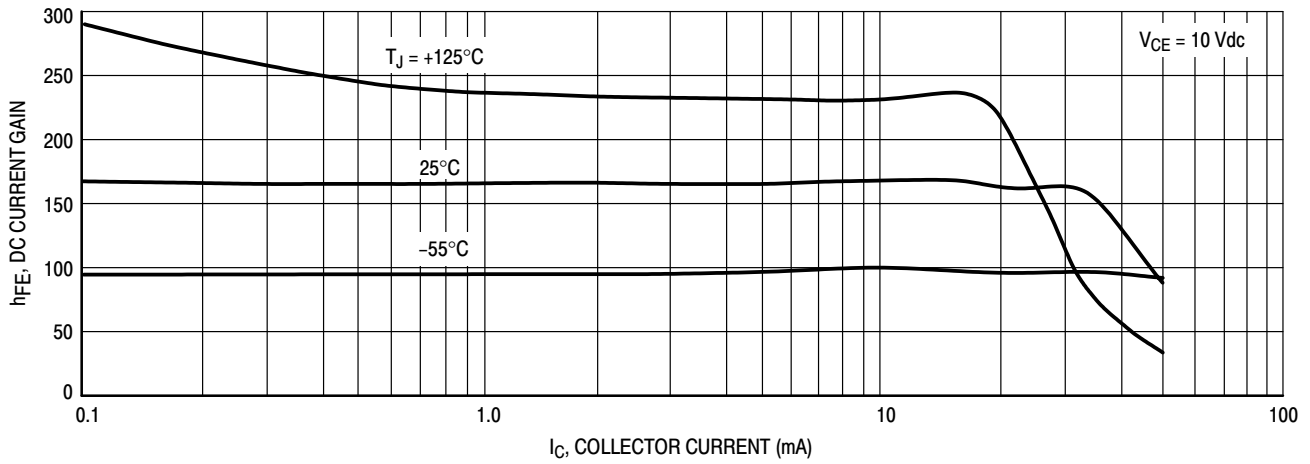


Figure 1. DC Current Gain

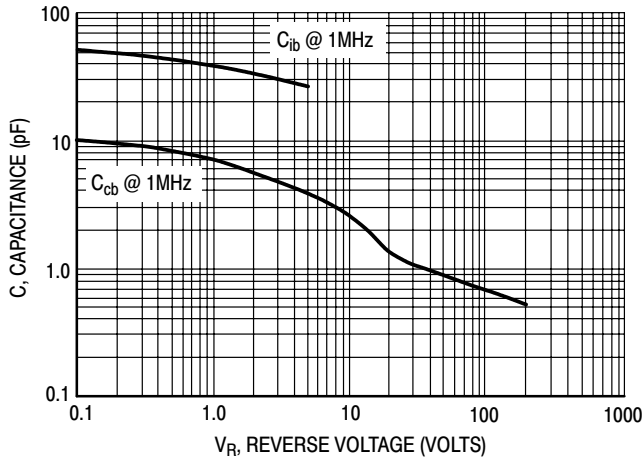


Figure 2. Capacitance

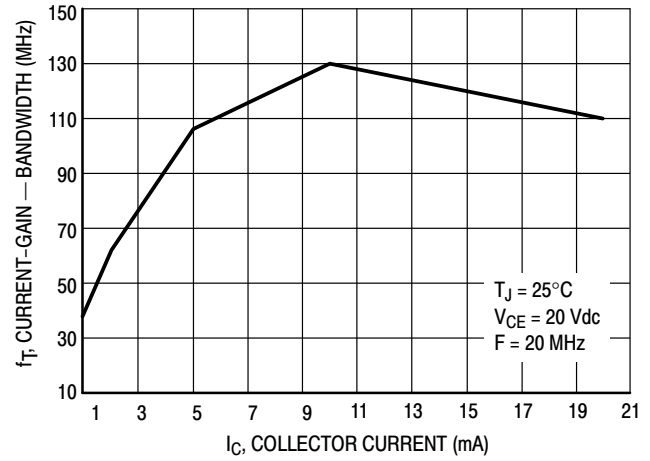


Figure 3. Current-Gain - Bandwidth

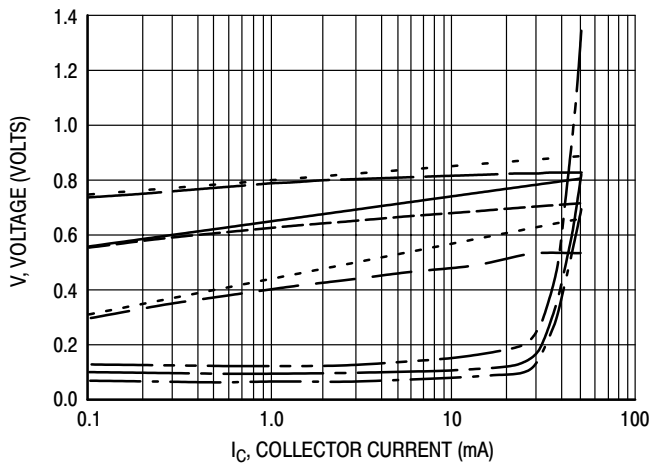


Figure 4. "ON" Voltages

- $V_{CE(sat)}$  @  $25^\circ\text{C}$ ,  $I_C/I_B = 10$
- $V_{CE(sat)}$  @  $125^\circ\text{C}$ ,  $I_C/I_B = 10$
- $V_{CE(sat)}$  @  $-55^\circ\text{C}$ ,  $I_C/I_B = 10$
- $V_{BE(sat)}$  @  $25^\circ\text{C}$ ,  $I_C/I_B = 10$
- $V_{BE(sat)}$  @  $125^\circ\text{C}$ ,  $I_C/I_B = 10$
- $V_{BE(sat)}$  @  $-55^\circ\text{C}$ ,  $I_C/I_B = 10$
- $V_{BE(on)}$  @  $25^\circ\text{C}$ ,  $V_{CE} = 10 \text{ V}$
- $V_{BE(on)}$  @  $125^\circ\text{C}$ ,  $V_{CE} = 10 \text{ V}$
- $V_{BE(on)}$  @  $-55^\circ\text{C}$ ,  $V_{CE} = 10 \text{ V}$

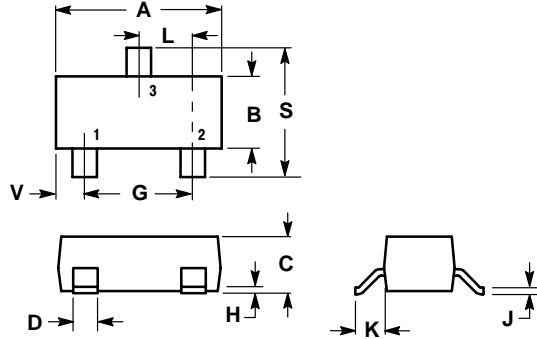
# MMBTA92LT1

## PACKAGE DIMENSIONS

SOT-23 (TO-236)  
CASE 318-08  
ISSUE AH

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318-03 AND -07 OBSOLETE, NEW STANDARD 318-08.



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

STYLE 6:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

### SOLDERING FOOTPRINT\*

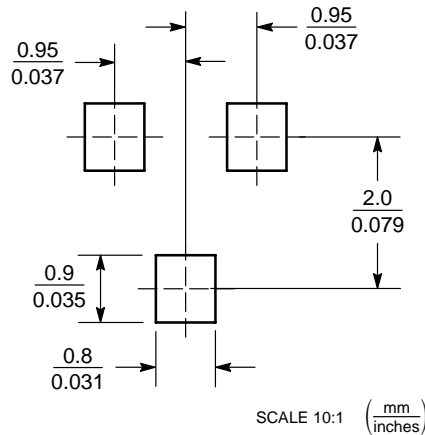


Figure 5. SOT-23

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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